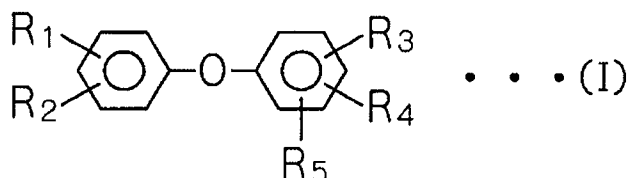


AMENDMENTS TO THE CLAIMS

1. **(Currently Amended)** A developer composition for resists, comprising an organic quaternary ammonium base as a main component,
said developer composition further comprising an anionic surfactant in an amount from 500 to 100,000 ppm represented by the following general formula (I):



wherein at least one of R_1 and R_2 represents an alkyl or alkoxy group having 5 to 18 carbon atoms and the other one represents a hydrogen atom, or an alkyl or alkoxy group having 5 to 18 carbon atoms, and at least one of R_3 , R_4 and R_5 represents an ammonium sulfonate group or a sulfonic acid-substituted ammonium group and the others represent a hydrogen atom, an ammonium sulfonate group or a sulfonic acid-substituted ammonium group;

SO_4^{2-} in an amount from 10 to 10,000 ppm; and

a lower alcohol in an amount from 0.05 to 2.5% by mass; ~~and~~

~~a halogen ion in an amount of 1,000 ppm or less.~~

2. **(Canceled)**

3. **(Canceled)**

4. **(Previously presented)** A method for formation of a resist pattern, comprising applying a resist composition on a substrate to form a resist layer, prebaking the resist layer, selectively exposing the prebaked resist layer to light, and alkali-developing the exposed resist layer with the developer composition for resists according to claim 1 to form a resist pattern.

5. **(Previously presented)** The developer composition for resists according to claim 1, wherein said lower alcohol has 1 to 5 carbon atoms.

6. **(Previously presented)** The developer composition for resists according to claim 5, wherein the lower alcohol is ethanol or methanol.

7. **(New)** The developer composition for resists according to claim 1, wherein the amount of said organic quaternary ammonium base is 0.1 to 10% by mass based on the developer composition for resists.

8. **(New)** The developer composition for resists according to claim 1, further comprising a halogen ion in an amount of 1,000 ppm or less.

9. **(New)** The developer composition for resists according to claim 8, wherein the amount of the halogen ion is from 300 to 1,000 ppm.